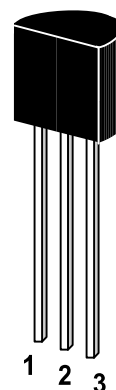


# ST 2SA1024

PNP Silicon Epitaxial Planar Transistor  
for high voltage applications.

The transistor is subdivided into two groups, O and Y  
according to its DC current gain.

On special request, these transistors can be  
manufactured in different pin configurations.



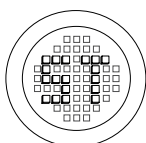
1. Emitter 2. Collector 3. Base

TO-92 Plastic Package  
Weight approx. 0.19g

## Absolute Maximum Ratings (T<sub>a</sub> = 25° )

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	150	V
Collector Emitter Voltage	$-V_{CEO}$	150	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	50	mA
Emitter Current	$I_E$	50	mA
Power Dissipation	$P_{tot}$	1000	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_s$	-55 to +150	°C

G S P FORM A IS AVAILABLE



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РАДИОТЕХ

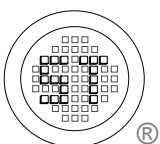
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# ST 2SA1024

## Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=5\text{V}$ , $-I_C=10\text{mA}$ Current Gain Group O Y	$h_{FE}$	70	-	140	-
	$h_{FE}$	120	-	240	-
Collector Cutoff Current at $-V_{CB}=150\text{V}$	$-I_{CBO}$	-	-	0.1	$\mu\text{A}$
Emitter Cutoff Current at $-V_{EB}=5\text{V}$	$-I_{EBO}$	-	-	0.1	$\mu\text{A}$
Gain Bandwidth Product at $-V_{CE}=30\text{V}$ , $-I_C=10\text{mA}$	$f_T$	-	120	-	MHz
Output Capacitance at $-V_{CB}=10\text{V}$ , $f=1\text{MHz}$	$C_{OB}$	-	4	5	pF
Base Emitter Voltage at $-V_{CE}=5\text{V}$ , $-I_C=30\text{mA}$	$-V_{BE}$	-	-	0.9	V
Collector Saturation Voltage at $-I_C=10\text{mA}$ , $-I_B=1\text{mA}$	$-V_{CE(sat)}$	-	-	0.8	V

**G S P FORM A IS AVAILABLE**



**SEMTECH ELECTRONICS LTD.**

(Subsidiary of Semtech International Holdings Limited, acompany  
listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002  
Certificate No. 05103



ISO 14001  
Certificate No. 7116



ISO 9001 : 2000  
Certificate No. 000-199-01-002-001

Dated : 07/12/2002